

Mark: 3R

PNP Switching Transistor

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	15	V
V _{EBO}	Emitter-Base Voltage	4.5	V
l _c	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		2N5771	*MMBT5771	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

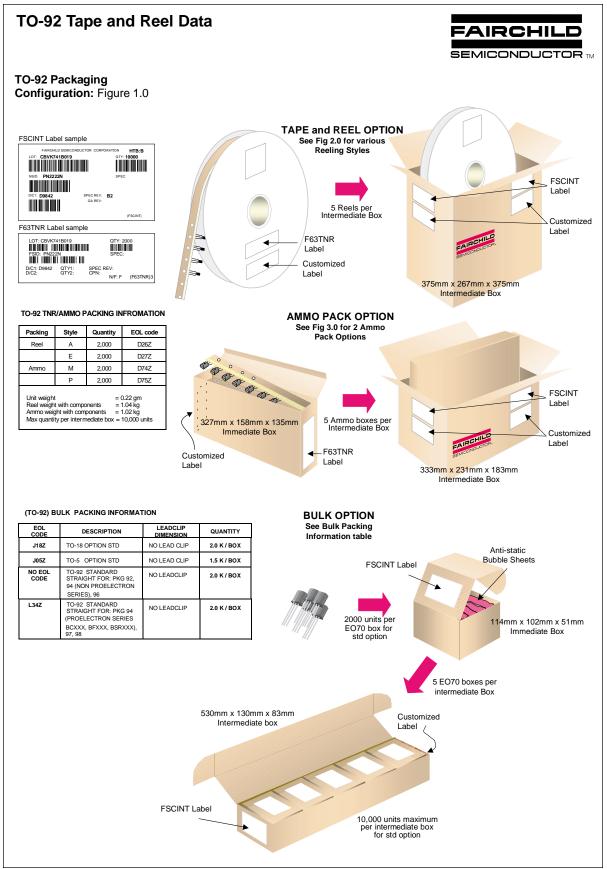
*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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PNP Switching Transistor (continued)

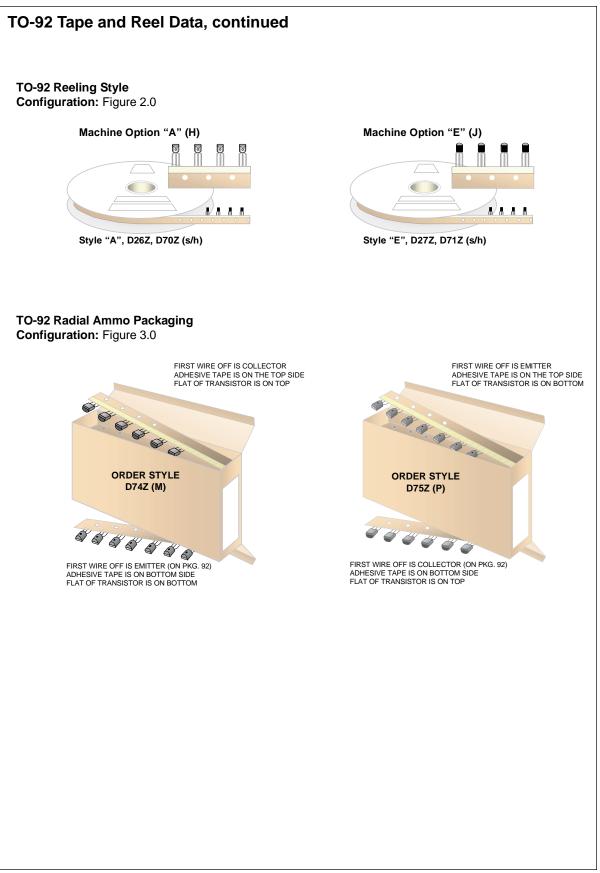
ACTERISTICS Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 3.0$ mA, $I_{\rm B} = 0$			
Collector-Emitter Breakdown Voltage*	L = 30 m A L = 0			
	$1_{\rm C} = 3.0$ [I]A. $1_{\rm B} = 0$	15	1	V
Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \mu\text{A}, V_{\rm BE} = 0$	15		V
Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu{\rm A}, I_{\rm E} = 0$	15		V
Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu{\rm A}, I_{\rm C} = 0$	4.5		V
	-		10	nA
				nA
			-	μA
Emitter Cutoff Current	$V_{EB} = 4.5 \text{ V}, I_{C} = 0$		1.0	μΑ
DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}, T_{A} = -55^{\circ}\text{C}$ $I_{C} = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	35 50 20 40	120	
Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$		0.15	V
	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		0.18	V
Page Emitter Seturation Voltage				V V
Dase-Emilier Saturation Voltage		0.75		v
	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		1.5	V
NAL CHARACTERISTICS	$V_{CB} = 5.0 \text{ V}, I_{E} = 0,$		3.0	pF
-	f = 140 kHz			
Emitter-Base Capacitance			3.5	pF
Small-Signal Current Gain	I = 140 KHZ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	8.5		MHz
GCHARACTERISTICS				
Storage Time			20	ns
Turn-On Time	$I_{C} = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ $I_{B} = 1.0 \text{ mA}$		15	ns
Turn-Off Time	$I_{C} = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ $I_{B1} = I_{B2} = 1.0 \text{ mA}$		20	ns
	Collector Cutoff Current Collector Cutoff Current Emitter Cutoff Current CTERISTICS* DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage NAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance Small-Signal Current Gain CCHARACTERISTICS Storage Time Turn-On Time	Collector Cutoff Current $V_{CB} = 8.0 \text{ V}, I_E = 0$ Collector Cutoff Current $V_{CE} = 8.0 \text{ V}, V_{BE} = 0, T_A = 125^{\circ}\text{C}$ Emitter Cutoff Current $V_{EB} = 4.5 \text{ V}, I_C = 0$ CTERISTICS*DC Current Gain $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}, I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$ Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ Base-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B 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Saturation Voltage $I_C = 1.0 \text{ mA}, I_B = 1.0 \text{ mA}$ 0.75 0.95 $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ 0.75 0.95 1.5 NAL CHARACTERISTICS Collector-Base Capacitance $V_{CB} = 0.5 \text{ V}, I_C = 0,$ 3.0 1.5 Small-Signal Current Gain $I_C = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ 8.5 1.5 Storage Time $I_C = 10 \text{ mA}, V_{CC} = 1.5 V$</td></td<>	Collector Cutoff Current $V_{CB} = 8.0 \text{ V}, I_E = 0$ Collector Cutoff Current $V_{CE} = 8.0 \text{ V}, V_{BE} = 0$ $V_{CE} = 8.0 \text{ V}, V_{BE} = 0, T_A = 125^{\circ}\text{C}$ Emitter Cutoff Current $V_{EB} = 4.5 \text{ V}, I_C = 0$ CTERISTICS*DC Current Gain $I_C = 1.0 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$ 40Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 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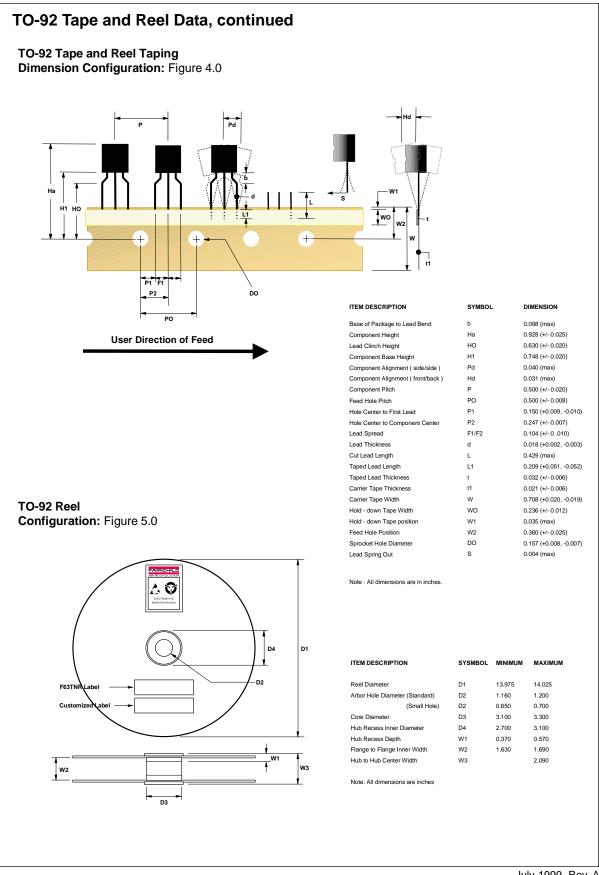
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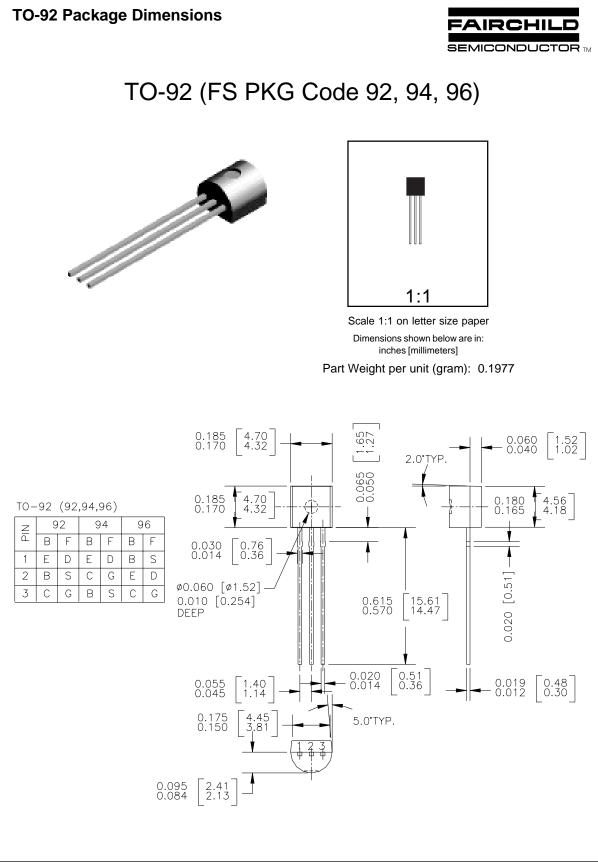
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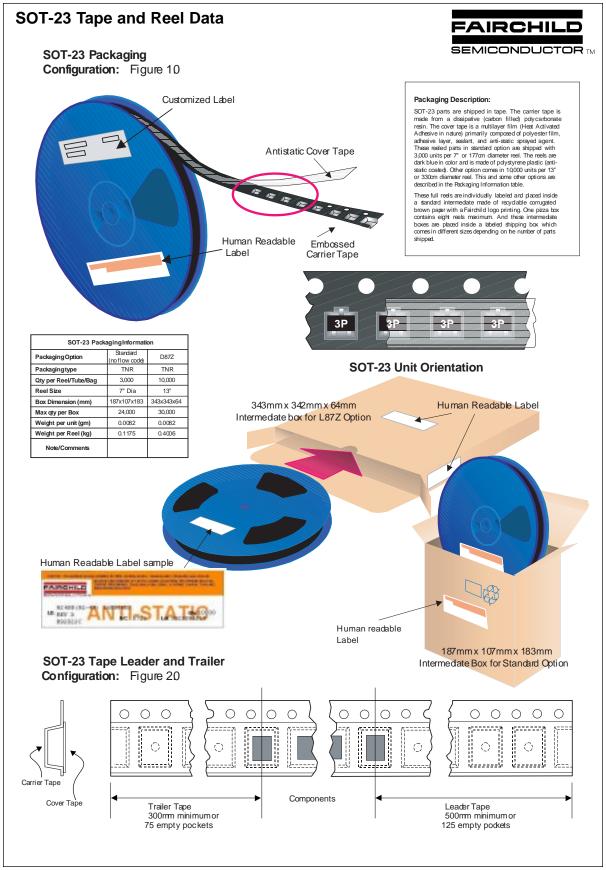
March 2001, Rev. B1





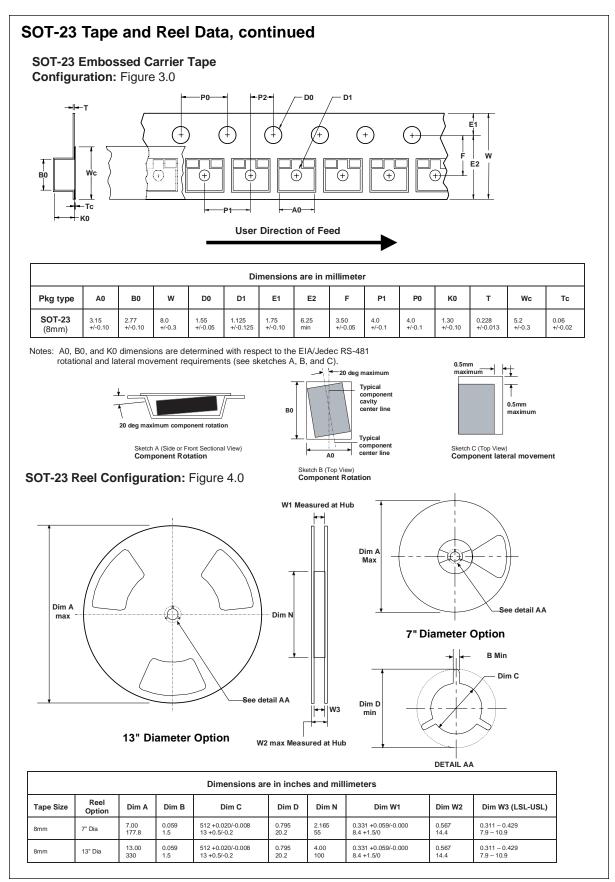
July 1999, Rev. A



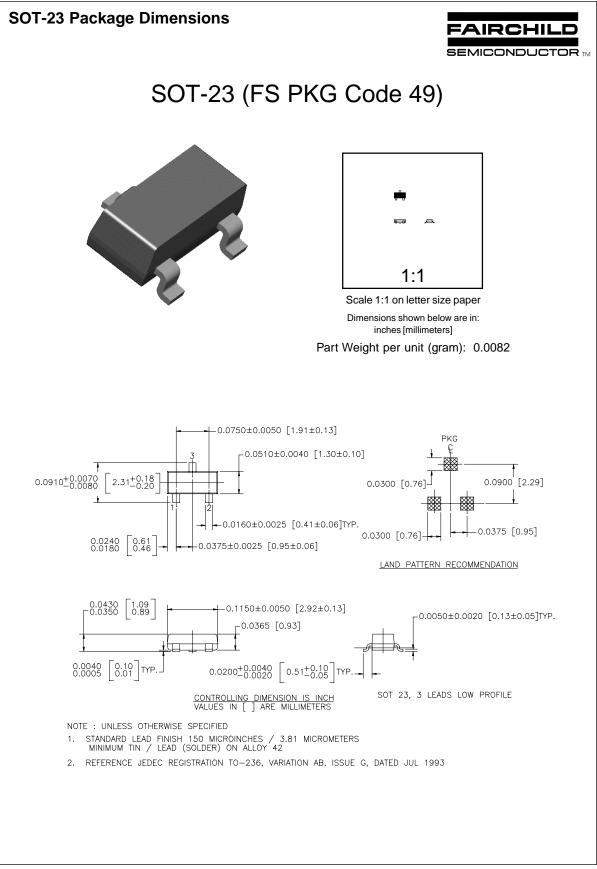


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